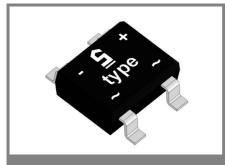
CS 10S ... CS 50S ...



Surface mount Schottky

Туре	Repetitive peak reverse voltage	Surge peak reverse voltage	Max. reverse recovery time I _F = A I _R = A I _{RR} = A	Max. forward voltage
	V_{RRM}	V_{RSM}	t _{rr}	
	V	V	ns	$V_F^{2)}$
CS 10S	20	20	1	< 0,50
CS 20S	40	40	1	< 0,50
CS 30S	60	60	1	< 0,70
CS 40S	80	80	1	< 0,79
CS 50S	100	100	1	< 0,79

Bridge rectifiers

CS 10S ... CS 50S

Forward Current: 1 A

Reverse Voltage: 10 to 50 V

Publish Data

Features

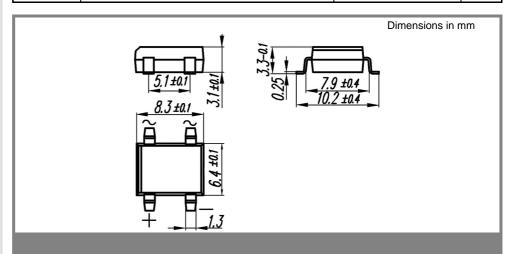
Standard packaging taped and reeled

Mechanical Data

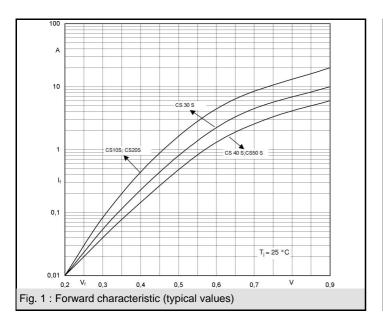
- Plastic case SO-DIL 8.5x6.6x3.1 mm
- Weight approx. 0.6 g
- 2) $I_F = 1A$, $T_j = 25^{\circ}C$

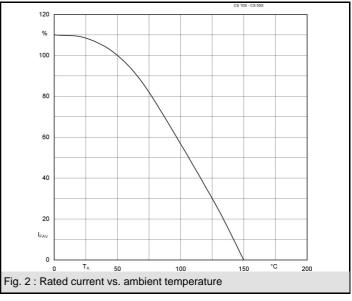
Absolute Maximum Ratings $T_c = 25^{\circ}\text{C}$ unless otherwise specified				
Symbol	Conditions	Values	Units	
I _{FAV}	Max. averaged fwd. current, R-load, T _A = 50 °C ¹⁾	1	Α	
I _{FRM}	Repetitive peak forward current f > 15 Hz ¹⁾	10	Α	
I _{FSM}	Peak forward surge current 50 Hz half sinus-wave 3)	40	Α	
i²t	Rating for fusing, t < 10 ms ³⁾	8	A²s	
R _{thA}	Max. thermal resistance junction to ambient 1)	60	K/W	
R _{thT}	Max. thermal resistance junction to terminals 1)		K/W	
T _j	Operating junction temperature	-50 +150°C	°C	
T _s	Storage temperature	-50 +150°C	°C	

Characte	racteristics $T_c = 25^{\circ}$ C unless otherwise spec		ecified
Symbol	Conditions	Values	Units
I _R	Maximum leakage current, $T_j = 25 ^{\circ}\text{C}$; $V_R = V_{RRM}$	0,5	mA
	$T_j = 100 ^{\circ}\text{C}; V_R = V_{RRM}$	5	mA
С	Typical junction capacitance (at MHz and applied reverse voltage of V)		pF
Q _{rr}	Reverse recovery charge $(U_R = V; I_F = A; dI_F/dt = A/ms)$		μC
E _{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA; T_j = ^{\circ}C;$ inductive load switched off)		mJ



CS 10S ... CS 50S ...





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